

PK(PD,PE)200GB

TOP



UL:E76102 (M)

Power Thyristor/Diode Module **PK200GB** series are designed for various rectifier circuits and power controls. For your circuit application, following internal connections and wide voltage ratings up to 800V are available.

Isolated mounting base

- $I_{T(AV)}$ 200A, $I_{T(RMS)}$ 310A, I_{TSM} 5500A
- di/dt 200 A/ μ s
- dv/dt 500V/ μ s

(Applications)

Various rectifiers

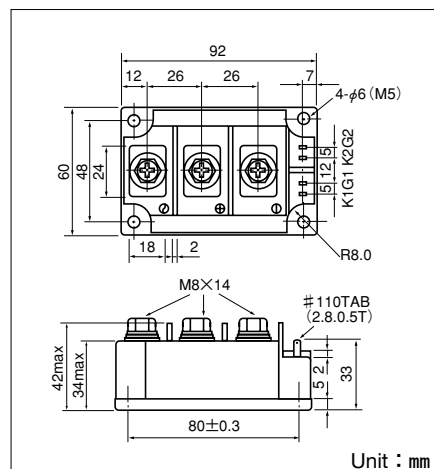
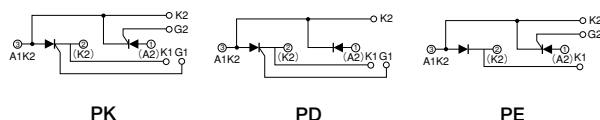
AC/DC motor drives

Heater controls

Light dimmers

Static switches

Internal Configurations



■ Maximum Ratings

Symbol	Item	Ratings		Unit
		PK200GB40 PE200GB40	PD200GB40 PK200GB80 PD200GB80	
V _{RRM}	* Repetitive Peak Reverse Voltage	400	800	V
V _{RSM}	* Non-Repetitive Peak Reverse Voltage	480	960	V
V _{DRM}	Repetitive Peak Off-State Voltage	400	800	V

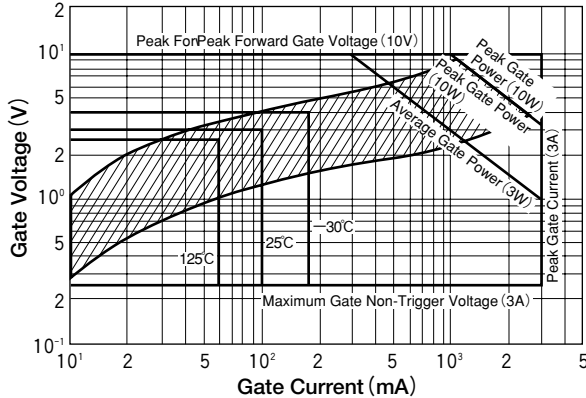
Symbol	Item		Conditions	Ratings	Unit
IT(AV)	* Average On-State Current		Single phase, half wave, 180° conduction, Tc : 74°C	200	A
IT(RMS)	* R.M.S. On-State Current		Single phase, half wave, 180° conduction, Tc : 74°C	310	A
ITSM	* Surge On-State Current		1/2 cycle, 50Hz/60Hz, peak Value, non-repetitive	5000/5500	A
I²t	* I²t		Value for one cycle of surge current	125000	A²S
PGM	Peak Gate Power Dissipation			10	W
PG(AV)	Average Gate Power Dissipation			3	W
IFGM	Peak Gate Current			3	A
VFGM	Peak Gate Voltage (Forward)			10	V
VRGM	Peak Gate Voltage (Reverse)			5	V
di/dt	Critical Rate of Rise of On-State Current		IG=100mA, Tj=25°C, VD=1/2VDRM, dIG/dt=0.1A/μs	200	A/μs
VISO	* Isolation Breakdown Voltage (R.M.S.)		A.C. 1 minute	2500	V
Tj	* Operating Junction Temperature			−40 to +125	°C
Tstg	* Storage Temperature			−40 to +125	°C
	Mounting Torque	Mounting (M5)	Recommended Value 1.5-2.5 (15-25)	2.7 (28)	N·m (kgf·cm)
		Terminal (M8)	Recommended Value 8.8-10 (90-105)	11 (115)	
	Mass		Typical Value	510	g

■Electrical Characteristics

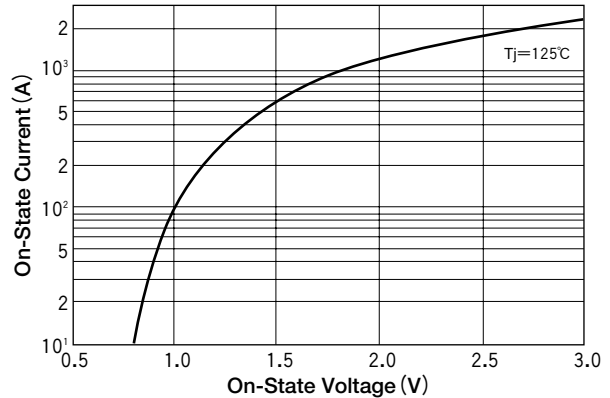
Symbol	Item	Conditions	Ratings	Unit
I _{DRM}	Repetitive Peak Off-State Current, max.	at V _{DRM} , Single phase, half wave, T _j =125°C	50	mA
I _{RRM}	* Repetitive Peak Reverse Current, max.	at V _{DRM} , Single phase, half wave, T _j =125°C	50	mA
V _{TM}	* Peak On-State Voltage, max.	On-State Current 600A, T _j =125°C Inst. measurement	1.50	V
I _{GT} /V _{GT}	Gate Trigger Current/Voltage, max.	T _j =25°C, I _T =1A, V _D =6V	100/3	mA/V
V _{GD}	Non-Trigger Gate, Voltage. min.	T _j =125°C, V _D =½V _{DRM}	0.25	V
t _{gt}	Turn On Time, max.	I _T =200A, I _G =100mA, T _j =25°C, V _D =½V _{DRM} , dI _G /dt=0.1A/μs	10	μs
dv/dt	Critical Rate of Rise of Off-State Voltage, min.	T _j =125°C, V _D =⅔V _{DRM} , Exponential wave.	500	V/μs
I _H	Holding Current, typ.	T _j =25°C	50	mA
I _L	Lutching Current, typ.	T _j =25°C	100	mA
R _{th} (j-c)	* Thermal Impedance, max.	Junction to case	0.18	°C/W

* mark : Thyristor and Diode part. No mark : Thyristor part

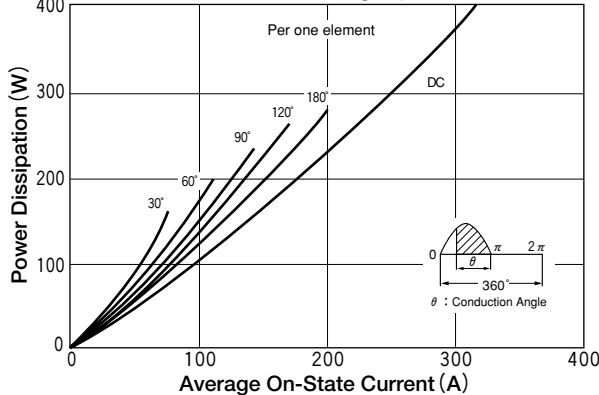
Gate Characteristics



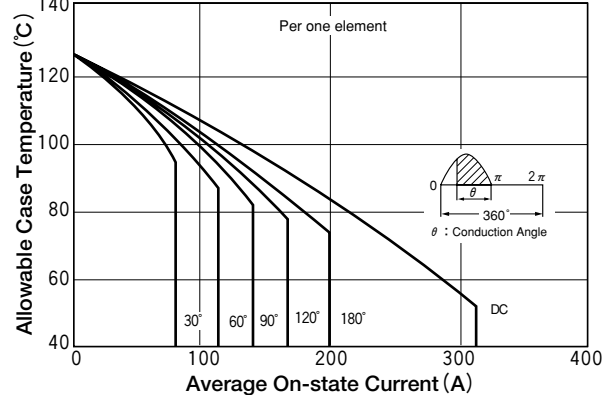
On-State Characteristics



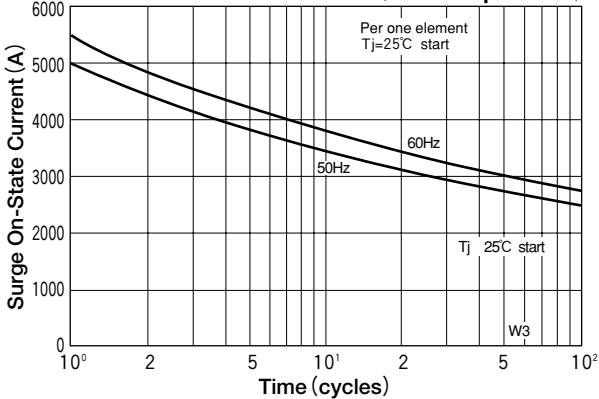
Average On-State Current Vs Power Dissipation (Single phase half wave)



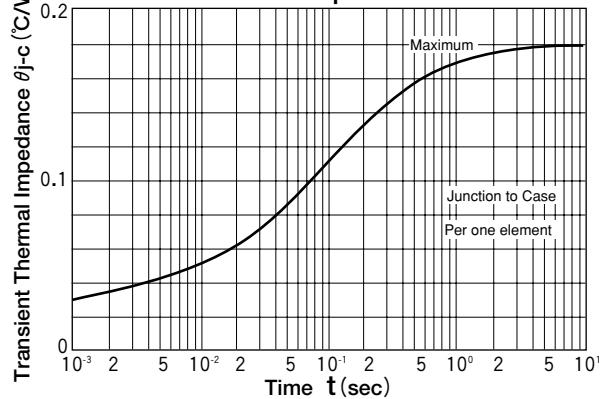
Average On-State Current Vs Maximum Allowable Case Temperature (Single phase half wave)



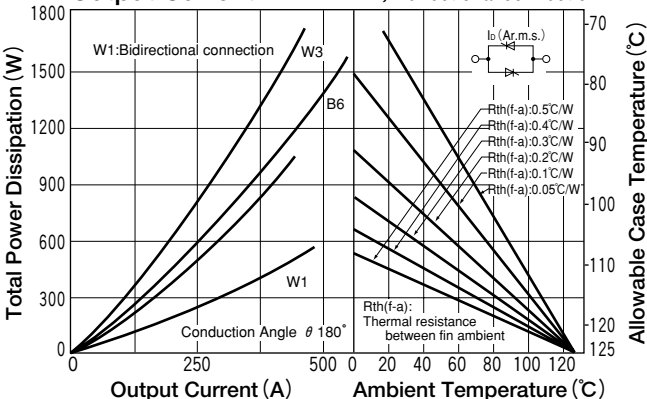
Surge On-State Current Rating (Non-Repetitive)



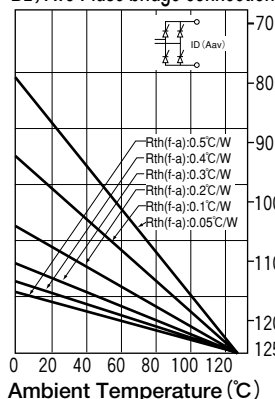
Transient Thermal Impedance



Output Current



B2;Two Pluse bridge connection



B6;Six pulse bridge connection W3;Three phase bidirectional connection

